

200mA, 40V Schottky Barrier Diode

FEATURES

- Low current rectification
- Low reverse current
- Surface mount device type
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I _F	200	mA	
V_{RRM}	40	V	
V _F at I _F =100mA	0.55	V	
T _{J MAX}	125	°C	
Package	SOD-523F		

APPLICATIONS

- Adapters
- For switching power supply
- · Low stored charge
- Inverter

MECHANICAL DATA

- Case: SOD-523F
- Molding compound meets UL 94 V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1A whisker test
- Polarity: Indicated by cathode band
- Weight: 1.60 mg (approximately)







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)			
PARAMETER	SYMBOL	RB520SM5-40	UNIT
Marking code on the device		D	
Power dissipation	P_D	200	mW
Repetitive peak reverse voltage	V_{RRM}	40	V
Non-repetitive peak reverse voltage	V_{RM}	40	V
Forward current	I _F	200	mA
Non-repetitive peak forward surge current @ t=8.3ms	I _{FSM}	1	А
Junction temperature range	TJ	-55 to +125	°C
Storage temperature range	T _{STG}	-55 to +125	°C

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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)					
PARAMETER CONDITIONS SYMBOL		SYMBOL	MIN	MAX	UNIT
Farmend maltage (1)	I _F = 10mA, T _J = 25°C			0.39	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Forward voltage (1)	$I_F = 100 \text{mA}, T_J = 25 ^{\circ}\text{C}$	V_F mA, $T_J = 25^{\circ}C$	_	0.55	V
Reverse voltage (2)	I _R = 100 μA, T _J = 25°C	V_R	40	-	V
Reverse current (2)	V _R = 10 V, T _J = 25°C	· I _R	-	1	μА
	$V_R = 40 \text{ V}, T_J = 25^{\circ}\text{C}$		_	10	

Notes:

- 1. Pulse test with PW=0.3 ms
- 2. Pulse test with PW=30 ms

ORDERING INFORMATION			
ORDERING CODE	ORDERING CODE PACKAGE		
RB520SM5-40 RSG	SOD-523F	8K / 7" Reel	



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Typical Forward Characteristics

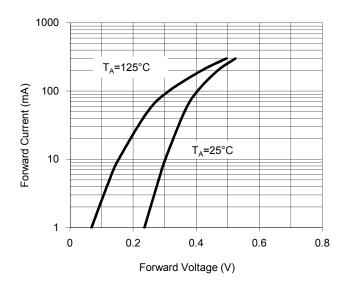


Fig.2 Typical Reverse Characteristics

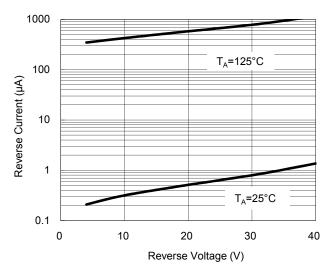


Fig.3 Typical Capacitance Characteristics

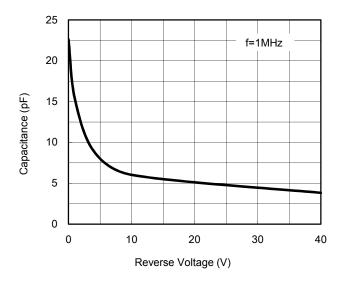
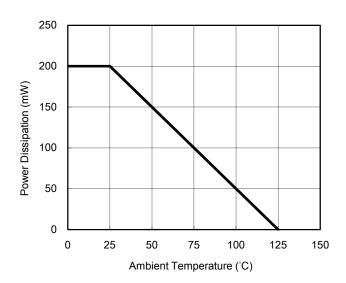


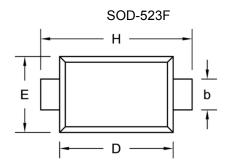
Fig.4 Power Derating Curve

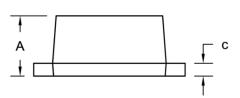




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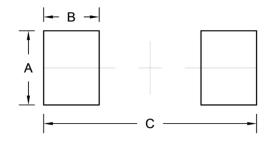
PACKAGE OUTLINE DIMENSION





DIM.	Unit (mm)		Unit (inch)	
DIIVI.	Min.	Max.	Min.	Max.
Α	0.50	0.77	0.020	0.030
b	0.25	0.40	0.010	0.016
С	0.07	0.20	0.003	0.008
D	1.10	1.30	0.043	0.051
Е	0.70	0.90	0.028	0.035
Н	1.50	1.70	0.059	0.067

SUGGEST PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
Α	0.80	0.031
В	0.60	0.024
С	2.30	0.091



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